

### MAINTENANCE MANUAL

# 406—512 MHz, 40 WATT POWER AMPLIFIER ASSEMBLY 19D424888G5-8, G22-25 AND G35, G36 (MOBILE & STATION) 19D424895G5-8, G22-25 AND G36, G37 (CONTINUOUS DUTY STATION)

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# DESCRIPTION

The PA assembly uses four RF power transistors to provide rated output power. R213, located on the PA module, is used to adjust the output power over a range of 12 Watts to rated output power. The power control circuit consists of R213, Q215, and Power Control IC (U201). Included in the PA assembly, is a Low Pass Filter/Antenna Switch module used to suppress undesired harmonic frequency components and provide antenna switching for the receiver and the transmitter.

# SUPPLY VOLTAGE

Supply voltage for the PA is connected through power leads from the system board to feed through capacitors C297 and C298 on the bottom of the PA assembly (See Schematic Diagram). C297, C298, and C299 prevent RF from getting on the power leads. Diode CR295 will cause the main fuse assembly to blow if the polarity of the power leads is reversed, providing reverse voltage protection for the radio.

The PA assembly is insulated from vehicle ground to permit operation in positive or negative ground vehicles.

NOTE\_

In positive ground vehicles, A- is "hot" with respect to vehicle ground. Shorting the transmitter PA printed wiring board ground pattern to the radio case may cause on of the in-line fuses to blow.

Centralized metering jack J205 is provided for use with GE Test Set Model 4EX3A11 or Test Kit 4EX8K12. The Test Set meters the Ampl-1 drive (exciter output), power control voltage, PA current and PA voltage.

# CIRCUIT ANALYSIS

RF POWER AMPLIFIER ASSEMBLY

The exciter output is coupled through a 50-ohm RF cable to the PA module input jack J201. The 50-ohm RF input is coupled through a matching network comprised of C206, C207, C208 and W202 to the base of power amplifier Q201.

Part of the RF input is rectified by CR201 and metered at J205-4 through resistor R201. The rectified RF is also applied to the power contol IC (U201).

Collector voltage for Q201 is applied direct from the DC power input through collector stabilizing network R205 and L202 and collector feed network L203 and C210.

The 500 milliwatt, 50-ohm output of Q201 is coupled to the base of a second power amplifier Q202 through a matching network consisting of T201, C214, C215, C216 and L204.

Collector voltage to Q202 is controlled by power control IC (U201), Q215 and R213 and is applied through a collector stabilizing network L206 and R206 and collector feed network L205 and C218.

The 6 Watt, 50-ohm output of Q202 is coupled to the base of Driver Amplifier



Q203 through C219 and the matching network of T202, C222, C224, C225 and L207. The collector voltage to Q203 is coupled through collector stabilizing network L209 and R214 and collector feed network L208 and C228.

The 20 Watt output of Q203 is coupled through an impedance matching network (C229, C230, C233 and T203) that matches the output impedance of Q203 to the input impedance of power amplifier Q204 through a 50-ohm micro strip (W204) and input impedance matching network T204, C234, C235 and C236.

The collector voltage for Q204 is coupled through collector stabilizing network L212 and R208 and collctor feed network C239 and L211. Supply voltage is measured in position F on the 15 volt range with the polarity switch in the (-) position (read as 15 Volts full scale).

Collector current for Q204 is metered across taped manganin resistor R212. The reading taken in position F on the 15 Volt scale with the High Sensitivity button pressed and read as 0-15 amperes full scale.

Following power amplifier Q204 to the 50-ohm input of the Low Pass Filter Module through 50-ohm micro stip W205 and a 50-ohm cable W218.

The input to the Low Pass Filter to the antenna switch K201 is coupled through the 50-ohm micro stirp W4280. The output is applied to the antenna at J203.

## WARNING

The RF Power Transistor used in the transmitter contains Beryllium Oxide, a TOXIC substance. If the ceramic or other encapsulation is opened, crushed, broken or abraded, the dust may be hazardous if inhaled. Use care in replacing transistors of this type.

### POWER CONTROL CIRCUIT

The Power Control Circuit, located on the PA module, consists of CR201, Power Control IC (U201), RT201, Q215 and R213.

When the transmitter is keyed, rectified RF from CR201 is applied to Switch Q1 of Power Control IC (U201), turning it on (See Figure 1). Turning on Q1 turns on

voltage regulator Q2, supplying a constant voltage via Pin 14 to Power Adjust potentiometer R213. R213 through Pin 12 connect to the base of Q5. Q5. Q6 and Q215 operate as an amplifier chain to supply voltage to the collector of Q202 (Ampl-2). The setting of R213 determines the voltage applied to the base of Q5. The higher the voltage at the base of Q5, the harder the amplifiers conduct, supplying more collector voltage to Q202. The lower the voltage at the base of Q5, the less collector voltage is supplied to Q202. Reducing the supply voltage to Q202 reduces the drive to Q203 and Q204, thereby reducing the power output of the PA. The power output can be adjusted by R213 from 12 Watts to rated power output.

Temperature protection is provided by Q3, Q4 in IC U201 and thermistor RT201 which is mounted on the PA heatsink. Under normal operating conditions, the circuit is inactive (Q3 is on and Q4 is off). When the heatsink temperature reaches approximately 115°C the resistance of RT201 decreases. This increases the base voltage applied to Q3, turning it off. Turning off Q3 allows Q4 to turn on, decreasing the voltage at Power Adjust potentiometer R213. This reduces the base voltage to Q5 which causes Q6 and Q215 to conduct less, reducing the collector voltage to Q202 (Ampl-2). This reduces the transmitter output power, keeping the heatsink at a maximum of approximately 115°C. When the heatsink temperature decreases below 115°C, the temperature control circuit turns off, allowing the normal transmitter power output.

### ANTENNA MATCHING UNIT

The Antenna Matching Unit is used only in continuous duty duplex stations to optimize impedance matching between the power amplifier and the load. It consists of a Pi network (C2-C5 and L1) and a reverse directional coupler. RF from the low pass filter is applied to the Pi network through the reverse directional coupler and then to the duplexer load. The reverse directional coupler permits monitoring the reflected power by connecting a DC voltmeter across TP1 (+) and ground (-). C2 and C4 are tuned for minimum DC voltage which represents reflected Power. L1 may also be pushed toward or away from the filter cover wall to further reduce the DC voltage. C2, C4, and L1 should be alternately tuned until an absolute minimum voltage reading is obtained. The residual voltage reading after tuning may vary from one transmitter to the next depending on output power level, operating frequency, and the load.

GENERAL ELECTRIC COMPANY+ MOBILE COMMUNICATIONS DIVISION WORLD HEADQUARTERS+LYNCHBURG, VIRGINIA 24502 U.S.A.



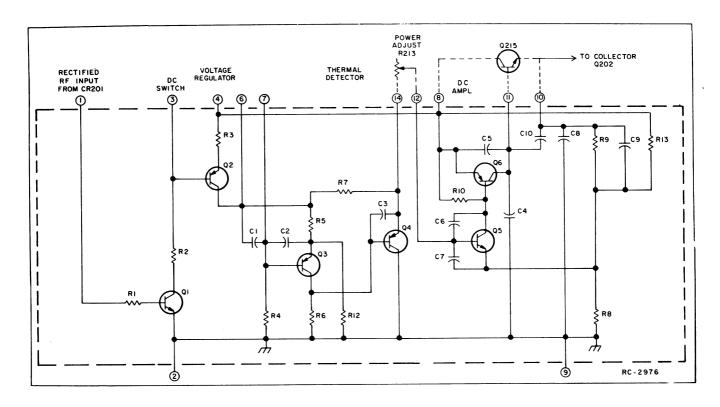
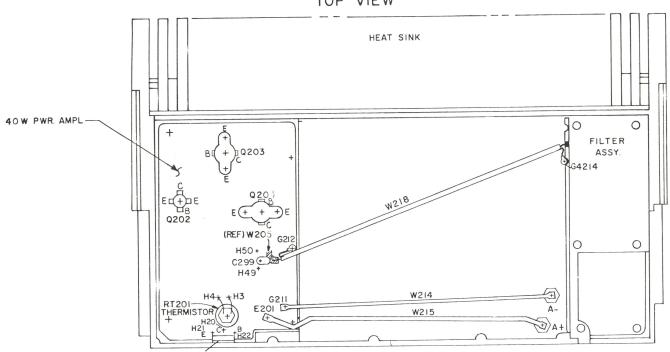


Figure 1 - Power Control IC - U201

# PA ASSEMBLY

# TOP VIEW



CAUTION

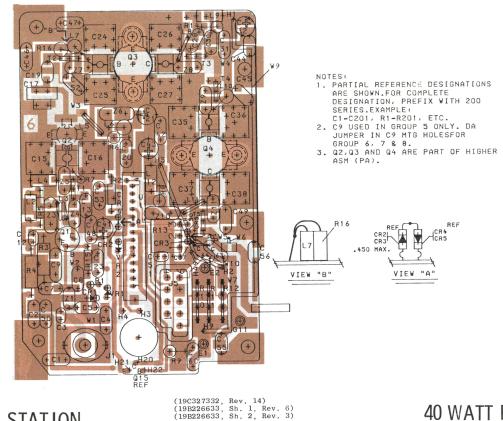
BLACK-CR295 RED + C297

(19D424207, Rev. 3)

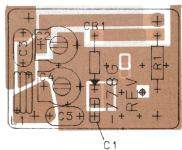
C299

# 40 WATT PA MODULE

TOP

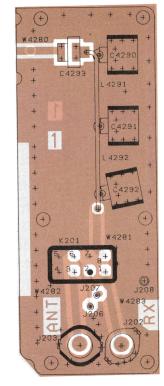


# ANTENNA MATCHING (DUPLEX STATIONS) UNIT

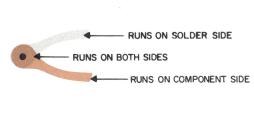


(19B233800, Rev. 0) (19A143200, Sh. 1, Rev. 0) (19A143200, Sh. 2, Rev. 0)

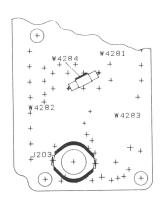
# MOBILE & STATION FILTER BOARD



(19C327643, Rev. 1) (19B227265, Sh. 1, Rev. 1) (19B227265, Sh. 2, Rev. 1)

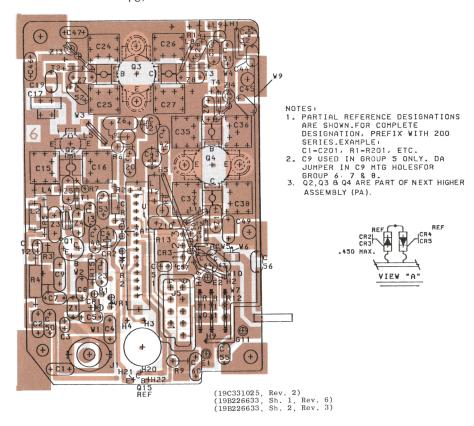


# DUPLEX STATION FILTER BOARD



# 40 WATT PA MODULE

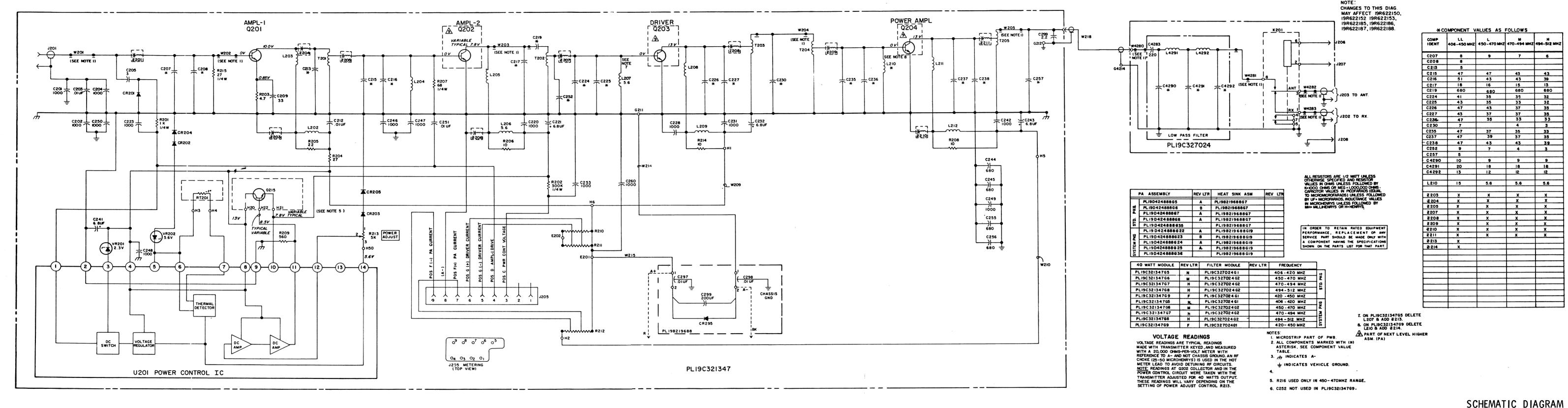
TOP



# OUTLINE DIAGRAM

40 WATT POWER AMPLIFIER

Issue 8



SCHEMATIC DIAGRAM

40 WATT POWER AMPLIFIER

# PARTS LIST

		PARTS LIST	SYMBOL	GE PART NO.	DESCRIPTION	
		LBI30214H	C207L*	19A116656P9J0	Ceramic disc: 9 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.	
	19D424888G5-G8, G3	2 MHz, 40 WATT POWER AMPLIFIER 35 ("M" SERIES MOBILE, INT. DUTY STATION) G36 ("E" SERIES MOBILE)		19A116656P6J0	In REV D & earlier:  Ceramic disc: 6 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.	
			C207M*	19A116656P7J0	Ceramic disc: 7 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.	
SYMBOL	GE PART NO.	DESCRIPTION		19A116656P6J0	In REV E & earlier:  Ceramic disc: 6 pF ±0.5 pF, 500 VDCW, temp coef	
		0.000	С207Н	19A116656P6J0	О РРМ.	
C299*	19A134100P20				Ceramic disc: 6 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.	
		PPM. Added to G6 & G23 by REV B.	C208LL	19A116656P8J0	Ceramic disc: 8 pF ±0.5 pF, 500 VDCW; temp coef 0 PPM.	
			C208L*	19A116656P6J0	Ceramic disc: 6 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM. Deleted by REV E.	
G212 G4214	7878455P2 7878455P2	Solderless terminal. Solderless terminal.	C208M*	19A116656P6J0	Ceramic disc: 6 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM. Deleted by REV F.	
	701040012	Solderless terminar.	C208H*	19A116656P6J0	Ceramic disc: 6 pF ±0.5 pF, 500 VDCW, temp coef	
			C209*	19A116656P33J0	0 PPM. Deleted by REV F.  Ceramic disc: 33 pF ±5%, 500 VDCW, temp coef 0	
Q202	19A134164P2	Silicon, NPN; sim to Type 2N5945.			PPM. Added to G5 by REV G, G6 by REV E, G7 & G8 by REV F.	
Q203LL Q203L	19A134239P3 19A134239P1	Silicon, NPN. Silicon, NPN.	C209LL*	7489162P15	Silver mica: 33 pF ±5%, 500 VDCW; sim. to Sprague Type 118. Deleted by REV C. Added by REV D. Deleted by REV G.	
Q203M Q203H	19A134239P1 19A134239P1	Silicon, NPN. Silicon, NPN.	C209L*	7489162P11	Silver mica: 22 pF ±5%, 500 VDCW; sim to Sprague Type 118. Deleted by REV C.	
Q204LL	19A134242P3	Silicon, NPN.	C209M*	7489162P11	Silver mica: 22 pF ±5%, 500 VDCW; sim to Sprague	
Q204L	19A134242P3	Silicon, NPN.	С209Н*	7489162P13	Type 118. Deleted by REV C. Silver mica: 27 pF +5%, 500 VDCW; sim. to Sprague	
Q204H	19A134242P4	Silicon, NPN; 50 Watt.	C210LL*	19A134666P3	Type 118. Deleted by REV C.	
Q215	19A116753P1	Silicon, NPN.	CZIOLL	19813400023	Frequency network: selective, 400-500 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Deleted in G5 by REV L. Deleted in G9 by REV D.	
RT201	19A129379G1	Thermistor: 40K ohms $\pm 20\%$ , color code white; sim to Carborundum Type Mo $\overline{8}06J-5$ .	C210L*	19A134666P1	Prequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G6 by REV K.	
<b>W214</b>	19B226725G1	Jumper.	C210M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G7 by REV H.	
W215 W218	19B227074G1 19A130552G1	Jumper. Jumper.	C210H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G8 by REV H.	
		40 WATT MODULE	C211LL*	19A134666P3	Frequency network: selective, 400-500 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Deleted in G5 by REV L.	
		19C321347G5 406-420 MHz (LL) 19C321347G6 450-470 MHz (L) 19C321347G7 470-494 MHz (M) 19C321347G9 494-512 MHz (H) 19C321347G9 420-450 MHz (LL)	C211L*	19A134666P1	Deleted in G9 by REV D.  Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G6 by REV K.	
			C211M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G7 by REV H.	
C201 and C202	19A116655P20	Ceramic disc: 1000 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap.	C211H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G8 by REV H.	
C203	19A116192P1	Ceramic: 0.01 uF ±20%, 50 VDCW; sim to Erie 8121 SPECIAL.	C212	19A116192P1	Ceramic: 0.01 uF ±20%, 50 VDCW; sim to Erie 8121 SPECIAL.	
C204	19A116655P20	Ceramic disc: 1000 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap.	C213*	19A116656P4J0	Ceramic disc: 4 pF +0.5 pF, 500 VDCW, temp coef 0 PPM. Deleted by REV B.	
C205	19A116656P3J0	Ceramic disc: 3 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.	C213LL*	19A116656P5J0	Ceramic dis: 5 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM. Added by REV E. Deleted by REV M. Added	
C206*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G5 by REV L. Deleted in G6 by REV K. Delted in G7, G8 by REV H. Deleted in G9 by REV D.	C214LL*	19A134666P3	by REV N.  Frequency network: selective, 400-500 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Deleted in G5 by REV L. Deleted in G9 by REV D.	
		In 19C321347G5 off REV E & earlier: In 19C321347G6,G7,G8 REV C & earlier:	C214L*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron	
C207LL	19A116655P18 19A116656P8J0	Ceramic disc: 680 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap.  Ceramic disc: 8 pF ±0.5 pF, 500 VDCW; temp coef	C214M*	19A134666P1	TC501:NPO:240J:SLAC. Deleted in G6 by REV K.  Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron	
		0 PPM.	C214H*	19A134666P1	TC501:NPO:240J:SLAC. Deleted in G7 by REV H.  Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron	
	·				TC501:NPO:240J:SLAC. Deleted in G8 by REV H.	
			'	•		
4.						
	1		1		1	

DESCRIPTION

SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL
C215LL	19A700131P47	Metallized teflon: 47 pF ±2%, 250 VDCW.	C229M*
C215L	19A700131P47	Metallized teflon: 47 pF ±2%, 250 VDCW.	
C215M	19A700131P43	Metallized teflon: 43 pF ±2%, 250 VDCW.	C229H*
C215H	19A700131P43	Metallized teflon: 43 pF ±2%, 250 VDCW.	
C216LL	19A700131P51	Metallized teflon: 51 pF <u>+</u> 2%, 250 VDCW, temp coef -130 PPM	C230LL*
C216L	19A700131P43	Metallized teflon: 43 pF ±2%, 250 VDCW.	
C216M	19A700131P43	Metallized teflon: 43 pF ±2%, 250 VDCW.	
С216Н	19A700131P39	Metallized teflon: 39 pF ±2%, 250 VDCW.	
C217LL	19A116679P18D	Metallized teflon: 18 pF ±0.5 pF, 250 VDCW.	C230L*
C217L	19A116679P16D	Metallized teflon: 16 pF ±0.5 pF, 250 VDCW.	C230M
C217M	19A116679P15D	Metallized teflon: 15 pF ±0.5 pF, 250 VDCW.	C230m
C217H	19A116679P13D	Metallized teflon: 13 pF ±0.5 pF, 250 VDCW.	С230Н
C218*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G5 by REV L.	C231
		Deleted in G6 by REV K. Deleted in G7, G8 by REV H. Deleted in G9 by REV D.	C232
C219*	19A116655P18	Ceramic disc: 680 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap. Deleted in G6 by REV J. Addeed	C233L*
C219L*	19A116656P24J0	to G6 by REV M.  Ceramic disc: 24 pF ±5%, 500 VDCW, temp coef 0 PPM. Added to G6 by REV J. Deleted in G6 by	С233Н*
C220	19A116655P20	REV M.  Ceramic disc: 1000 pF ±10%, 1000 VDCW; sim to	C234LL*
		RMC Type JF Discap.	
C221	19B209723P4	Tantalum: 6.8 uF ±20%, 35 VDCW.	C234L*
C222LL*	19A134666P3	Frequency network: selective, 400-500 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Deleted in G5 by REV L. Deleted in G9 by REV D.	C234M*
C222L*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:MP0:240J:SLAC. Deleted in G6 by REV K.	C234H*
C222M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron	C235LL*
C222H*	19A134666P1	TC501:NPO:240J:SLAC. Deleted in G7 by REV H.  Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron	
C223	19A116655P20	TC501:NPO:240J:SLAC. Deleted in G8 by REV H.  Ceramic disc: 1000 pF ±10%, 1000 VDCW; sim to	C235L
C224LL	101500101041	RMC Type JF Discap.	C235M
C224LL	19A700131P41	Metallized teflon: 41 pF ±2%, 250 VDCW, temp coef 0 -130 PPM.	С235Н
C224L	19A700131P35	Teflon/mica: 35 pF ±2%, 250 VDCW.	C236LL*
C224M	19A700131P35	Teflon/mica: 35 pF ±2%, 250 VDCW.	1
C224H	19A700131P32	Metallized teflon: 32 pF ±2%, 250 VDCW.	1
C225LL	19A700131P43	Metallized teflon: 43 pF ±2%, 250 VDCW.	
C225L	19A700131P35	Teflon/mica: 35 pF ±2%, 250 VDCW.	C236L
C225M	19A700131P33	Metallized teflon: 33 pF ±2%, 250 VDCW.	C236M
С225Н	19A700131P32	Metallized teflon: 32 pF ±2%, 250 VDCW.	С236Н
C226LL	19A700131P47	Metallized teflon: 47 pF ±2%, 250 VDCW.	C237LL
C226L	19A700131P43	Metallized teflon: 43 pF ±2%, 250 VDCW.	C237L*
C226M	19A700131P37	Metallized teflon: 37 pF ±2%, 250 VDCW.	1
С226Н	19A700131P35	Teflon/mica: 35 pF <u>+</u> 2%, 250 VDCW.	
C227LL	19A700131P43	Metallized teflon: 43 pF ±2%, 250 VDCW.	C237M
C227L	19A700131P37	Metallized teflon: 37 pF ±2%, 250 VDCW.	C237H*
C227M	19A700131P37	Metallized teflon: 37 pF ±2%, 250 VDCW.	
C227H	19A700131P35	Teflon/mica: 35 pF ±2%, 250 VDCW.	1
C228	19A116655P20	Ceramic disc: 1000 pF ±10%, 1000 VDCW; sim to	C238LL
annov - :		RMC Type JF Discap.	C238L
C229LL*	19A134666P3	Frequency network: selective, 400-500 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Deleted in G5 by REV L. Deleted in G9 by REV D.	C238M*
C229L*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron	

SYMBOL	GE PART NO.	DESCRIPTION	SYN
C229M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G7 by REV H.	C238
C229H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:2400;SLAC. Deleted in G8 by REV H.	C239
C230LL*	19A116656P7J0	Ceramic disc: 7 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.	
		In G5 of REV M & earlier: In G9 of REV E & earlier:	C239
	19A116656P8J0	Ceramic disc: 8 pF ±0.5 pF, 500 VDCW; temp coef 0 PPM.	C240
C230L*	19A116656P4J0	Ceramic disc: 4 pF +0.5 pF, 500 VDCW, temp coef 0 PPM. Deleted by REV L.	
C230M	19A116656P4J0	Ceramic disc: 4 pF ±0.5 pF, 500 VDCW, temp coef	C240
С230Н	19A116656P3J0	O PPM.  Ceramic disc: 3 pF ±0.5 pF, 500 VDCW, temp coef	C240
C231	19A116655P20	0 PPM.  Ceramic disc: 1000 pF +10%, 1000 VDCW; sim to	02.10
		RMC Type JF Discap.	C240
C232	19B209723P4	Tantalum: 6.8 uF ±20%, 35 VDCW.	
C233L*	19A134100P20	Ceramic disc: 2.2 pF ±0.1 pF, temp coef 0 ±120 PPM. Deleted by REV B.	C241
C233H*	19A134100P20	Ceramic disc: 2.2 pF $\pm$ 0.1 pF, temp coef 0 $\pm$ 120 PPM. Deleted by REV B.	C242
C234LL*	19A134666P3	Frequency network: selective, 400-500 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Deleted in G5 by REV L.	C243 C244 and
C234L*	19A134666P1	Deleted in G9 by REV D.  Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G6 by REV K.	C245 C246 thru
C234M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron	C250
C234H*	19A134666P1	TC501:NPO:240J:SLAC. Deleted in G7 by REV H.  Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron	C252
C235LL*	19A700131P47	TC501:NPO:240J:SLAC. Deleted in G8 by REV H.  Metallized teflon: 47 pF ±2%, 250 VDCW.	
		In G5 of REV M & earlier: In G9 of REV E & earlier:	
	19A116952P43	Metallized teflon: 43 pF ±2%, 250 VDCW.	
C235L	19A700131P37	Metallized teflon: 37 pF ±2%, 250 VDCW.	
C235M	19A700131P35	Teflon/mica: 35 pF ±2%, 250 VDCW.	
С235Н	19A700131P33	Metallized teflon: 33 pF <u>+</u> 2%, 250 VDCW.	
C236LL*	19A700131P47	Metallized teflon: 47 pF ±2%, 250 VDCW.	C252
		In G5 of REV M & earlier: In G9 of REV E & earlier:	
	19A116952P39	Metallized teflon: 39 pF ±2%, 250 VDCW.	
C236L	19A700131P35	Teflon/mica: 35 pF ±2%, 250 VDCW.	
C236M	19A700131P33	Metallized teflon: 33 pF ±2%, 250 VDCW.	
C236H	19A700131P33	Metallized teflon: 33 pF ±2%, 250 VDCW.	
C237LL	19A700131P47	Metallized teflon: 47 pF ±2%, 250 VDCW.	
C237L*	19A700131P39	Metallized teflon: 39 pF ±2%, 250 VDCW.	
	19 <b>A</b> 116952P47	In REV K & earlier:  Metallized teflon: 47 pF ±2%, 250 VDCW.	C252
C237M	19A700131P37	Metallized teflon: 37 pF +2%, 250 VDCW.	C252
C237H*	19A700131P35	Teflon/mica: 35 pF ±2%, 250 VDCW.	(252
		In REV D & earlier:	C253
	19A116952P33	Metallized teflon: 33 pF ±2%, 250 VDCW.	C255
C238LL	19A700131P47	Metallized teflon: 47 pF ±2%, 250 VDCW.	and C256
C238L	19A700131P43	Metallized teflon: 43 pF ±2%, 250 VDCW.	C257
C238M*	19A700131P43	Metallized teflon: 43 pF ±2%, 250 VDCW.	
		In REV D & earlier:	
	19A116952P37	Metallized teflon: 37 pF ±2%, 250 VDCW.	
		1	

SYMBOL	GE PART NO.	DESCRIPTION	SYMB
C238H*	19A700131P39	Metallized teflon: 39 pF ±2%, 250 VDCW.	C257L
	104112050000	In REV D & earlier:	C257M
C239*	19A116952P33 19A134666P1	Metallized teflon: 33 pF ±2%, 250 VDCW.  Frequency network: selective, 470-630 MHz res.	C257H
C233	13413400071	freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted from G5 by REV H.	C260
C239LL*	7489162P13	Silver mica: 27 pF ±5%, 500 VDCW; sim. to Sprague Type 118. Added to G5 by REV H. Deleted in G5 by REV L. Deleted in G9 by REV D.	C262*
C240LL*	19A134666P3	Frequency network: selective, 400-500 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Deleted in G5 by REV L. Deleted in G9 by REV D.	C263* and C264*
C240L*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G6 by REV K.	
C240M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G7 by REV H.	CR201
C240H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G8 by REV H.	thru CR205
C241	19A134202P15	Tantalum: 6.8 uF +20%, 35 VDCW.	•
C242	19A116655P20	Ceramic disc: 1000 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap.	E201 and E202
C243	19A134202P15	Tantalum: 6.8 uF <u>+</u> 20%, 35 VDCW.	G211
C244 and C245	19A116655P18	Ceramic disc: 680 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap.	
C246 thru C250	19A116655P20	Ceramic disc: 1000 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap.	J201
C251	19A116192P1	Ceramic: 0.01 uF ±20%, 50 VDCW; sim to Erie 8121 SPECIAL.	J205
C252LL*	19A116656P5J0	Ceramic dis: 5 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.	L202
		In REV H-L:	L203
	19A116656P9J0	Ceramic disc: 9 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.	L204
		In REV B-G.	L205
	19A116656P6J0	Ceramic disc: 6 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.	L206 L207*
		In REV A & earlier:	L208L
	19A116656P4J0	Ceramic disc: 4 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.	L208L
C252L*	19A116656P7J0	Ceramic disc: 7 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.	L208M
		In REV L:	L208H L209
	19A116656P3J0	Ceramic disc: 3 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.	L210Li
		In REV J-K:	L210L
	19A116656P7J0	Ceramic disc: 7 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.	L210M
		In REV B-H:	L210H
	19A116656P5J0	Ceramic dis: 5 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.	L211
C252M*	19A116656P4J0	Ceramic disc: 4 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM. Added by REV B.	L212
C252H*	19A116656P3J0	Ceramic disc: 3 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM. Added by REV B.	Q201
C253	19A116655P20	Ceramic disc: 1000 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap.	
C255 and C256	19A116655P18	Ceramic disc: 680 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap.	R201 R202
C257LL*	19A116656P5J0	Ceramic dis: 5 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.	R203*
		In REV M:	R204*
	19A116656P7J0	Ceramic disc: 7 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.	
	19A116656P5J0	In REV L & earlier:  Ceramic dis: 5 pF ±0.5 pF, 500 VDCW, temp coef 0	

	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL
	C257L*	19A134100P20	Ceramic disc: 2.2 pF ±0.1 pF, temp coef 0 ±120 PPM. Deleted by REV B.	R205
	C257M*	19A134100P19	Ceramic disc: 1 pF ±0.1 pF, temp coef 0 ±250 PPM. Deleted by REV B.	R206 R207
res.	C257H*	19A134100P19	Ceramic disc: 1 pF ±0.1 pF, temp coef 0 ±250 PPM. Deleted by REV B.	R208
EV H.	C260	19A116655P20	Ceramic disc: 1000 pF ±10%, 1000 VDCW; sim to	R209
prague in G5	C262*	19A116114P2044	RMC Type JF Discap.  Ceramic: 27 pF ±5%, 100 VDCW; temp coef -80 PPM.	R210 thru R212
res.	C263*	19A116655P20	Added to G6 by REV F. Deleted by REV G.  Ceramic disc: 1000 pF ±10%, 1000 VDCW; sim to	R213
L.	and C264*		RMC Type JF Discap. Added to G5 by REV K. Added to G6 by REV H.	R214
res.			Added to G7 & G* by REV G. Added to G9 by REV C.	R215
к.	CR201	19A116052P1	DIODES AND RECTIFIERS	R216*
res.	CR201	19A115250P1	Silicon, hot carrier: Fwd drop .350 volts max. Silicon, fast recovery, 225 mA, 50 PIV.	
res.	thru CR205		, , , , , , , , , , , , , , , , , , , ,	T201
н.				thru T205
	E201	19A134263P1	Contact, electrical: sim to Selectro	
to	and E202		229-1082-00-0-590.	U201
	G211	19A134263P1	Contact, electrical: sim to Selectro 229-1082-00-0-590.	
to RMC				VR201
	J201	194700049P2	JACKS AND RECEPTACLES	VR202
i to		100100012	Connector, receptacle; 500 VDCW maximum; sim to NTTF-1058.	
e 8121	J205	19B219374G1	Connector: 9 contacts.	W201
coef 0				thru W205
	L202	19A701091G1	Coil.	W206
	L203 L204	19A129774P1 19A701091G1	Coil.	W209
coef	L204	19B219457P6	Coil.	W210
l	L206	19A700000P120	Coil, RF: 5.6 uH ±10%; sim to Jeffers 4422-1K.	
coef	L207*	19A700000P20	Coil, RF: 5.6 uH +10%; sim to Jeffers 4421-4K. Deleted in G5 by REV M, G9 by REV E.	Z201*
1	L208LL	19B219457P6	Coil.	
coef	L208L	19A130650P1	Coil.	Z203LL*
coef	L208M	19A130650P1	Coil.	
	L208H	19A130650P1	Coil.	Z203L*
coef	L209 L210LL*	19A701091G1	Coil DR. 15 cH 110% c/c to 7 cc 1401 CF	
	L210LL+	19A700000P25	Coil, RF: 15 uH ±10%; sim to Jeffers 4421-9K. Deleted by REV M.	Z203M*
coef	L210L	19A700000P20	Coil, RF: 5.6 uH <u>+</u> 10%; sim to Jeffers 4421-4K.	
	L210M	19A700000P20	Coil, RF: 5.6 uH ±10%; sim to Jeffers 4421-4K.	Z203H*
coef 0	L210H L211	19A700000P20 19B219457P6	Coil, RF: 5.6 uH <u>+</u> 10%; sim to Jeffers 4421-4K.	Z204LL*
	L212	19A701091G1	Coil.	
coef			TRAVO 2000	70041 *
coef	Q201	19A134237P1	Silicon, NPN.	Z204L*
to	`			Z204M*
	P201	101700100000		
to RMC	R201 R202	19A700106P63 3R152P304J	Composition: 1K ohms ±5%, 1/4 w.  Composition: 300K ohms ±5%, 1/4 w.	Z204H*
coef 0	R203*	19A700113P7	Composition: 4.7 ohms +5%, 1/2 w. Deleted by	
	P204*	104700112005	REV C. Added by REV D.	Z205LL*
coef	R204*	19A700113P25	Composition: 27 ohms ±5%, 1/2 w. In REV B & earlier:	
		3R77P220J	Composition: 22 ohms ±5%, 1/2 w.	Z205L*
		\$ 		
coef 0			,	

	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPT
R205 R206	19A700106P23	Composition: 22 ohms ±5%, 1/4 w.  Composition: 10 ohms ±5%, 1/2 w.	Z205M*	19A134666P1	Frequency network: selecting, 500 VDCW; sim to Ditection TC501:NPO:240J:SLAC. Add
R207	19A700106P35	Composition: 68 ohms ±5%, 1/4 w.	Z205H*	19A134666P1	Frequency network: selectreq, 500 VDCW; sim to Di
208	19A700113P15 19A700113P57	Composition: 10 ohms ±5%, 1/2 w.  Composition: 560 ohms ±5%, 1/2 w.	Z206*	19A134666P1	TC501:NPO:240J:SLAC. Add
210 hru 212	19C850605P1	Shunt resistor.			freq, 500 VDCW; sim to Di TC501:NPO:240J:SLAC. Adde Added to G6 by REV K. Add Added to G9 by REV D.
R213	19A116559P102 19A700113P15	Variable cermet: 5000 ohms $\pm 20\%$ , 1/2 w; sim to CTS Series 360.  Composition: 10 ohms $\pm 5\%$ , 1/2 w.	Z207LL*	19A134666P3	Frequency network: selectined, 500 VDCW; sim to Ditto: TC501:NPO:330J:SLAC. Added to G9 by REV D.
R215 R216*	19A700106P25 19A700113P15	Composition: 27 ohms ±5%, 1/4 w.  Composition: 10 ohms ±5%, 1/2 w. Added to G6 by	Z207L*	19A134666P1	Frequency network: selec freq, 500 VDCW; sim to Di TC501:NPO:240J:SLAC. Add
		REV F. Deleted by REV L.	Z207M*	19A134666P1	Frequency network: selectifreq, 500 VDCW; sim to Di TC501:NPO:240J:SLAC. Adde
T201 thru T205	19A130446G1	Coil.	Z207H*	19A134666P1	Frequency network: selec freq, 500 VDCW; sim to Di TC501:NPO:240J:SLAC. Add
U201	19D423127G1	INTEGRATED CIRCUITS	Z208LL*	19A134666P3	Frequency network: selectifreq, 500 VDCW; sim to Dit TC501:NPO:330J:SLAC. Added to G9 by REV D.
0001	102 130131 01	VOLTAGE REGULATORS	Z208L*	19A134666P1	Frequency network: selectined, 500 VDCW; sim to Di TC501:NPO:240J:SLAC. Adde
VR201 VR202	4036887P1 4036887P5	Zener: 500 mW, 2.3 v. nominal.  Zener: 500 mW, 5.4 v. nominal.	Z208M*	19A134666P1	Frequency network: selective freq, 500 VDCW; sim to Di. TC501:NPO:240J:SLAC. Adde
W201 thru			Z208H*	19A134666P1	Frequency network: select freq, 500 VDCW; sim to Di TC501:NPO:240J:SLAC. Adde
W205 W206	19A701093P1	Strap.	Z209LL*	19A134666P3	Frequency network: selecting, 500 VDCW; sim to Di
/209 /210	19B226733G1 19B226734G1	Jumper. Jumper.	Z209L*	19A134666P1	Added to G9 by REV D.  Frequency network: selecting, 500 VDCW; sim to Dil
201*	19A134666P1		Z209M*	19A134666P1	TC501:NPO:240J:SLAC. Added Frequency network: select freq, 500 VDCW; sim to Di TC501:NPO:240J:SLAC. Added
		freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G5 by REV L. Added to G6 by REV K. Added to G7, G8 by REV H. Added to G9 by REV D.	Z209H*	19A134666P1	Frequency network: selectifreq, 500 VDCW; sim to Dil TC501:NPO:240J:SLAC. Adde
203LL*	19A134666P3	Frequency network: selective, 400-500 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Added to G5 by REV L. Added to G9 by REV D.	Z210*	19A134666P1	Frequency network: select freq, 500 VDCW; sim to Di TC501:NPO:240J:SLAC. Adde Added to G6 by REV K. Add
Z203L*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G6 by REV K.	Z211LL*	19A134666P3	Added to G9 by REV D.  Frequency network: selectory, 500 VDCW; sim to Di
Z203M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G7 by REV H.	Z211L*	19A134666P1	TC501:NPO:330J:SLAC. Added Added to G9 by REV D.  Frequency network: selecting, 500 VDCW; sim to Ditermination.
Z203H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G8 by REV H.	Z211M*	19A134666P1	TC501:NPO:240J:SLAC. Add Frequency network: selectreq, 500 VDCW; sim to Di
Z204LL*	19A134666P3	Frequency network: selective, 400-500 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Added to G5 by REV L. Added to G9 by REV D.	Z211H*	19A134666P1	TC501:NPO:240J:SLAC. Adde Frequency network: selectreq, 500 VDCW; sim to Di
Z204L*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G6 by REV K.	Z212*	19A134666P1	TC501:NPO:240J:SLAC. Add Frequency network: selectined, 500 VDCW; sim to Di
Z204M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G7 by REV H.			TC501:NPO:240J:SLAC. Adde Added to G6 by REV K. Add Added to G9 by REV D.
Z204H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G8 by REV H.	Z213* and Z214*		NETWORK AS 19A14358 (Added to G5 by REV
Z205LL*	19A134666P3	Frequency network: selective, 400-500 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Added to G5 by REV L.			INDUC
	19A134666P1	Added to G9 by REV D.  Frequency network: selective, 470-630 MHz res.	L1	19A700024P1	Coil, RF: 100 nH ±10%, 0

SYMBOL	GE PART NO.	DESCRIPTION
Z205M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G7 by REV H.
Z205H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G8 by REV H.
Z206*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G5 by REV L. Added to G6 by REV K. Added to G7, G8 by REV H. Added to G9 by REV B.
Z207LL*	19A134666P3	Frequency network: selective, 400-500 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Added to G6 by REV L. Added to G9 by REV D.
Z207L*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G6 by REV K.
Z207M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G7 by REV H.
Z207H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to 68 by REV H.
Z208LL*	19A134666P3	Frequency network: selective, 400-500 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Added to G5 by REV L.
Z208L*	19A134666P1	Added to G9 by REV D.  Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:2400:SLAC. Added to G6 by REV K.
Z208M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G7 by REV H.
Z208H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:2400:SLAC. Added to 68 by REV H.
Z209LL*	19A134666P3	Frequency network: selective, 400-500 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Added to G5 by REV L. Added to G9 by REV D.
Z209L*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to 66 by REV K.
Z209M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:2400:SLAC. Added to G7 by REV H.
Z209H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:2400:SLAC. Added to G8 by REV H.
Z210*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G5 by REV L. Added to G6 by REV K. Added to G7, G8 by REV H. Added to G9 by REV D.
Z211LL*	19A134666P3	Frequency network: selective, 400-500 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Added to G5 by REV L. Added to G9 by REV D.
Z211L*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G6 by REV K.
Z211M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:2400:SLAC. Added to G7 by REV H.
Z211H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G8 by REV H.
Z212*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G5 by REV L. Added to G6 by REV K. Added to G7, G8 by REV H. Added to G9 by REV D.
Z213* and Z214*		NETWORK ASSEMBLY 19A143581G1 (Added to G5 by REV M, G9 by REV E)
L1	19A700024P1	
L2	19A701091G2	v. Coil.

SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION
		RESISTORS	J206 and		(Part of K201).
R1	19A700106P15	Composition: 10 ohms ±5%, 1/4 w.	J207		
	15 00100110	composition. To ching you, 1/1 w.	J208	4033513P4	Contact, electrical: sim to Bead Chain L93-3.
		LOW PASS FILTER 19C327024G1 406-450 MHz (LL) 19C327024G2 450-512 MHz (H)			
		19C327024G2 450-512 MHz (H) (Added to 19D424888 by REV A)	K201	19A116722P1	Hermetic sealed: 125 ohms ±20%, 1 form C contact, 9.6 to 15.8 VDC (over the temp range indicated). (Includes J206 & J207).
C4290LL	19A700014P4	Metallized teflon: 10 pF ±5%, 250 VDCW.	ļ		
С4290Н	19A700131P9	Metallized teflon: 9 pF ±0.5 pF, 250 VDCW.	W4280 thru		(Part of printed board 19D423316P1).
C4291LL C4291H	19A700131P20	Metallized teflon: 20 pF ±0.5 pF, 100 VDCW.	W4283		
C4291h C4292LL	19A700131P18 19A700131P13	Metallized teflon: 18 pF ±0.5 pF, 250 VDCW.  Metallized teflon: 13 pF ±0.5 pF, 250 VDCW.			HEAT SINK 19B219688G7 "M" SERIES
C4292H	19A700131P12	Teflon: 12 pF ±0.5 pF, 250 VDCW.			19B219688G19 "E" SERIES
C4293	19A700015P37	Teflon/Mica: 220 pF +5%, 250 VDCW.			
			C297	19A116708P1	Ceramic, feed-thru: 0.01 uF +100%-0%; sim to
7 400177	100000000		and C298		Erie Style 327050X-5W0103P.
L4291LL L4291H	19B226709G2 19B226709G1	Jumper. (Includes L4292LL).  Jumper. (Includes L4292H).	C299	19A115680P10	Electrolytic: 220 uF +150%-10%, 18 VDCW; sim to Mallory Type TTX.
L4292LL	10022010001	(Part of L4291LL).			
L4292H		(Part of L4291H).			DIODES AND RECTIFIERS
			CR295	19A116783P1	Rectifier, silicon: 100 VDC blocking, 6 amps.
J202	19A700049P2				MISCELLANEOUS
and J203	194700049P2	Connector, receptacle; 500 VDCW maximum; sim to NTTF-1058.		5492178P2	Washer, spring tension: sim to Wallace Barnes 375-20. (Used with Q202).
J206	19A134263P2	Contact, electrical: sim to Selectro 229-1071.		19A702182P1	Spacer. (Used with Q202).
and J207				19A702782P5	Nut, hex, brass: No. 8-32. (Used with Q202).
J208	4033513P4	Contact, electrical: sim to Bead Chain L93-3.		N44P9010C6	Machine screw: No. 4-40 x 5/8. (Used with Q203, Q204).
				19A700068P1	Insulator, bushing. (Used with Q215).
K201	19A700061P1	Hermetic sealed: 180 to 341 ohms coil res,		19A116023P1	Insulator, plate. (Used with Q215).
		8-16.3 VDC; sim to GE 3SAV1760A2, CP Clare HFW-1201558, or Potter-Brumfield HCM6160.		19B201074P312	Tap screw, Phillips POZIDRIV®: No. 6-32 x 3/4. (Secures Mobile Filter Assembly).
				19B201074P306	Tap screw, Phillips POZIDRIV®: No. 6-32 x 3/8.
W4280		(Part of printed board 19D423812P1).			(Secures Filter Board).
thru W4283				19C321441P1	Insulator. (Located under 40 watt Module).
				19D416732G7	Heat sink. ("M" SERIES).  Heat sink. ("E" SERIES).
		LOW PASS FILTER MODULE 19C321424G1 406-450 MHZ (LL)		19A129639P1	Cover, Heat Sink Assembly. ("E" SERIES).
		19C321424G2 450-512 MHZ (H) (Deleted on 19D424888 by REV A)		19A701332P4	Insulator, washer: nylon. (Used with Q201).
				N80P9006C6	Machine screw: No. 4-40 x 3/8. (Secures Q215
C4280LL	19A700014P4			714122502	Mobile).  Hex nut: No. 4-40. (Secures Q215).
C4280LL C4280H	19A700014P4 19A700131P9	Metallized teflon: 10 pF ±5%, 250 VDCW.  Metallized teflon: 9 pF ±0.5 pF, 250 VDCW.		N403P35C6	Washer, steel: No. 4. (Secures Q215).
C4281LL	19A700131P20	Metallized teflon: 20 pF ±0.5 pF, 100 VDCW.		N80P13010C6	Machine screw: No. 6-32 x 5/8. (Secures Mobile
C4281H	19A700131P18	Metallized teflon: 18 pF +0.5 pF, 250 VDCW.			40 Watt Module).
C4282LL	19A700131P13	Metallized teflon: 13 pF ±0.5 pF, 250 VDCW.			
C4282H	19A700131P12	Teflon: 12 pF ±0.5 pF, 250 VDCW.			
C4283LL	19A700015P37	Teflon/Mica: 220 pF ±5%, 250 VDCW.			
C4283H	19A700015P37	Teflon/Mica: 220 pF ±5%, 250 VDCW.			
L4281	19B226709G1	Jumper. (450-512 MHz).			
L4282	19B226709G2	Jumper. (406-450 MHz).			
J202 and	19A700049P2	JACKS AND RECEPTACLES Connector, receptacle; 500 VDCW maximum; sim to			·
J203					

Changes in the equipment to improve performance or to simplify circuits are identified by a "Revision Letter," which is stamped after the model number of the unit. The revision stamped on the unit includes all previous revisions. Refer to the Parts List for descriptions of parts affected by these revisions.

REV. A - PA Assembly 19D424888G5-G8, G22-G25

To incorporate new low-pass filter. Deleted 19C321424. Added 19C327024.

REV. B - 40 Watt Module 19C321347G5-G8

To improve operation. Added C209 and R203.

To improve station operation. Added C213.

REV. F - 40 Watt Module 19C321347G5

To improve operation. Changed C206

REV. G - 40 Watt Module 19C321347G5

REV. F - 40 Watt Module 19C321347G7, G8

REV. H - 40 Watt Module 19C321347G5

To increase output at 406 MHz. Changed C252LLB. Deleted C239. Added C239LLB.

To improve stability. Added R216 and C262.

REV. G - To improve operation. Deleted C262.

REV. B - To improve stability. Changed Q203LL.

REV. K - 40 Watt Module 19C321347G5

REV. C - 40 Watt Module 19C321347G9

REV. L - 40 Watt Module 19C321347G5

REV. H - 40 Watt Module 19C321347G8

REV. D - 40 Watt Module 19C321347G9

To improve power output. Added C299.

To increase power output. Changed C252LB and C237. Deleted R216 and C230.

To improve power output over the 450-470 MHz range. Changed C219L and C252L.

# **PRODUCTION CHANGES**

REV. A - 40 Watt Module 19C321347G5-G8

To improve power output at cold temperatures. Added CR204 & CR205.

To improve operation.
In 19C321347G5: deleted C213 and changed C252LLB.
In 19C321347G6: deleted C233L, C257L and added C252LB.
In 19C321347G7: deleted C257M and added C252MB.
In 19C321347G8: deleted C233H, C257H and added C252HB.

REV. C - 40 Watt Module 19C321347G5-G8

To improve operation. Deleted C209 and R203. Changed R204.

REV. D - 40 Watt Module 19C321347G5

REV. E - 40 Watt Module 19C321347G5

REV. D - 40 Watt Module 19C321347G6-G8

To improve operation. Changed C206

REV. E - 40 Watt Module 19C321347G7, G8

To improve RF output and efficiency. Changed C237 (Group 8) and C238 (Groups 7 & 8).

REV. E - 40 Watt Module 19C321347G6

To decrease spurious outputs. Changed C207L, M and C209. Deleted C208L, M, H. Added R203 to Groups 6, 7 and 8.

REV. J - To improve stability. Changed Q203LL.

REV. F - 40 Watt Module 19C321347G6

REV. A - 40 Watt Module 19C321347G9

To improve operation. Added C240LL.

REV. H - 40 Watt Module 19C321347G6

REV. G - 40 Watt Module 19C321347G7

REV. G - 40 Watt Module 19C321347G8

To improve operation of power regulator circuit when used as driver for 100 Watt PA. Added C263 and C264.

REV. J - 40 Watt Module 19C321347G6

To increase output power at low end of 450-470 MHz range. Changed C252.

REV. K - 40 Watt Module 19C321347G6 REV. H - 40 Watt Module 19C321347G7

To incorporate new nomenclature for frequency selection networks.

REV. B - PA Assembly 19D424895G6, G23

REV. M - 40-Watt Module 19C321347G5 REV. E - 40-Watt Module 19C321347G9

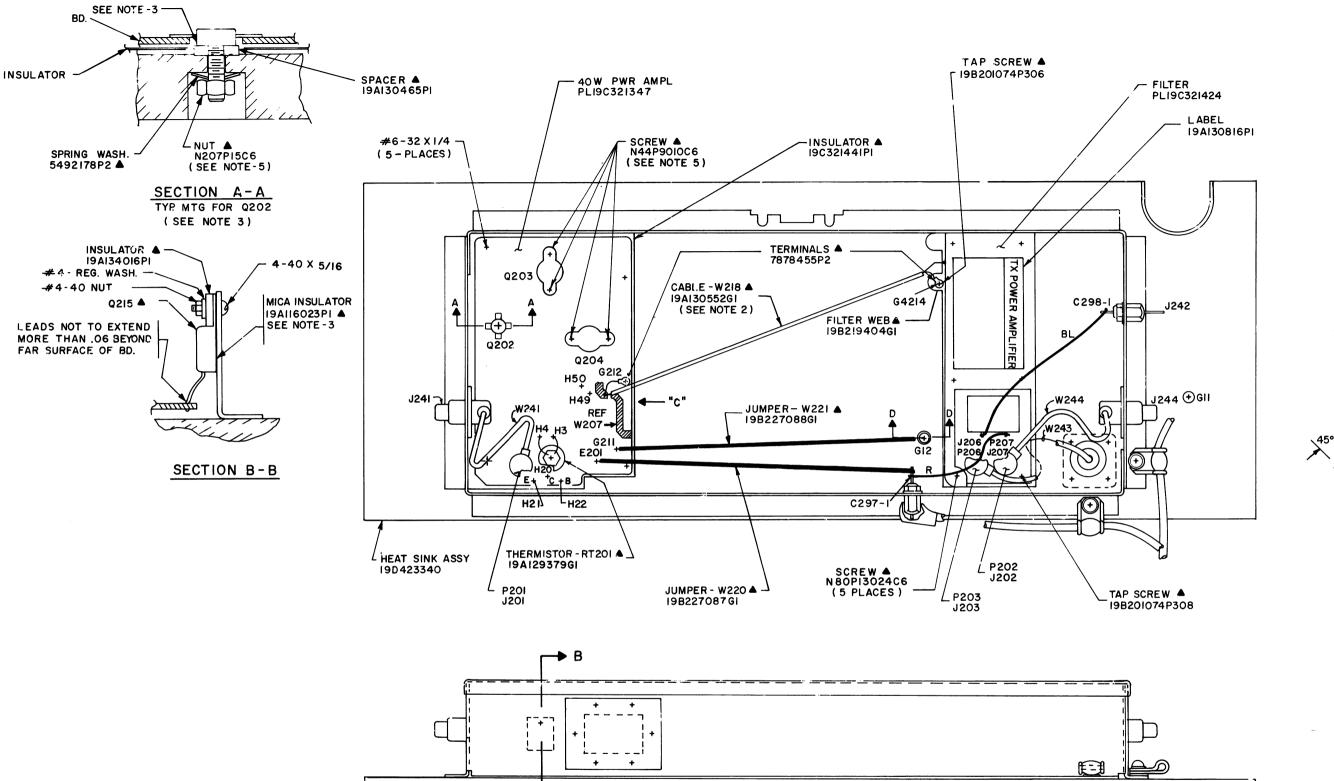
To improve power output across the board. Deleted C213LL, L207, and L210LL. Added Z213 and Z214. Changed C257LL, C252LLB (Group 5 only), and Q203LLB.

REV. N - 40-Watt Module 19C321347G5 REV. F - 40-Watt Module 19C321347G9

To improve power output. Changed C230LL, C235LL, C236LL and C257LL. Added C213LL.

REV. L - 40-Watt Module 19C321347G6

REV. M - 40-Watt Module 19C321347G6



(19D423350, Sh. 2, Rev. 5)

# 40 W UHF PA

2 NOTES:
1. ▲ PART OF KIT 19A130484.

2. CENTER CONDUCTOR OF W218 MUST BE SOLDERED TO W205 IN AREA INDICATED. NOTE: GROUND BRAID OF W218
MUST NOT TOUCH GROUND ON 40W MODULE (19C321347).

3. APPLY SILICONE GREASE TO BOTH SURFACES OF TRANSISTOR INSULATOR (194116023P1), BETWEEN BOTH MTG SURFACES
OF SPACER (194130465P1) & BETWEEN MTG. SURFACE OF RT201 Q203, Q204 & HEAT SINK PER CPD PROCESS P6A-EAIII. CARE MUST BE USED SO THAT NO GREASE IS APPLIED TO THE THREADED PORTION OF THE MTG. STUD OF Q202.

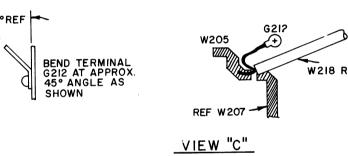
LBI30213

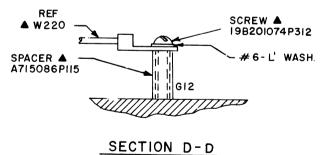
4. SOLDER ALL ELECTRICAL CONNECTIONS.

5. TIGHTEN TRANSISTOR MTG. HARDWARE TO WITHIN 8 ± 1 IN. LBS. FOR #8 HARDWARE & 6 ± 1 IN. LBS. FOR #4 HARDWARE

6. RECOMMENDED INSTALLATION PROCEDURE OF 40 WATT MODULE (1903/1347) 15: ASSEMBLE ALL HARDWARE LOOSE THEN TORQUE Q202, THEN TORQUE Q203 AND Q204 THEN TIGHTEN MOUNTING HARDWARE

7. SEE INTERCONNECTION DIAG 19R622186.

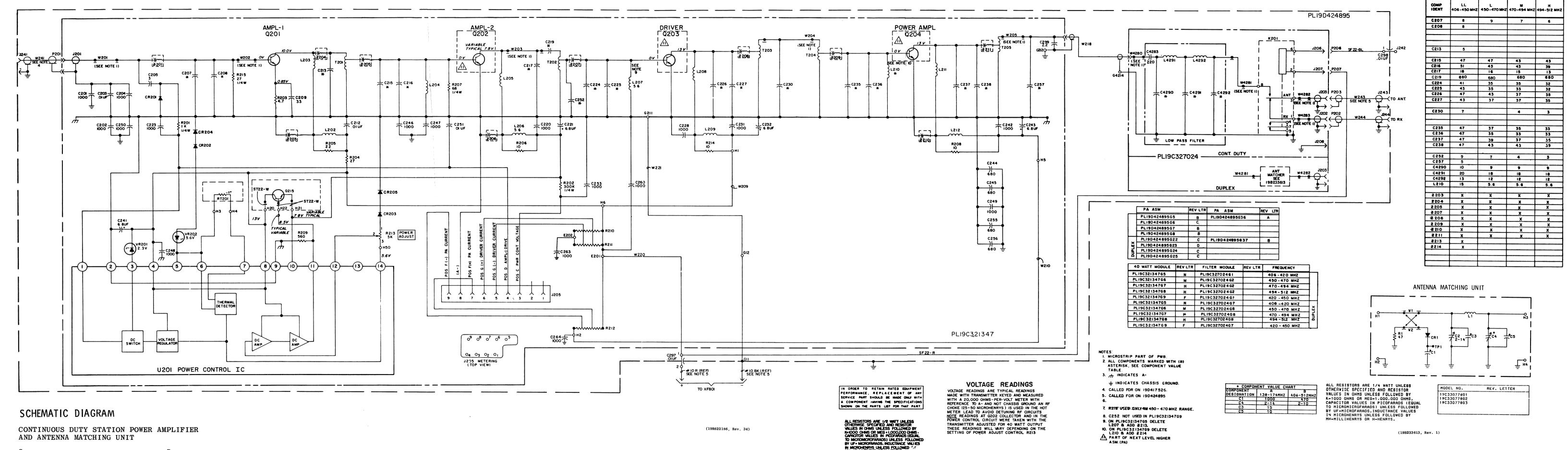




OUTLINE DIAGRAM

CONTINUOUS DUTY STATION POWER AMPLIFIER AND ANTENNA MATCHING UNIT

Issue 5



Issue 9

# LBI30213

		PARTS LIST			
LBI30594G					
	406-512	MHz, 40 WATT POWER AMPLIFIER			
19D424895G5-G8, G36 (CONTINUOUS DUTY) 19D424895G22-G25, G37 (CONTINUOUS DUTY - DUPLEX)					
SYMBOL	GE PART NO.	DESCRIPTION			
C297 and C298	19A116708P1	Ceramic: 0.01 uF -0 +100%, 500 VDCW, rated 20 amps; sim to Erie 327050X5W0103P.			
C299*	19A134100P20	Ceramic disc: 2.2 pF ±0.1 pF, temp coef 0 ±120 PPM. Added to G6 by REV C, G23 by REV D.			
G212 and G213	7878455P2	Solderless terminal.			
G4214	7878455P2	Solderless terminal.			
		JACKS AND RECEPTACLES			
J243	5491689P108	Connector/cable: approx. 10 inches long.			
		PLUGS			
P203		Connector. Includes receptacle and adaptor.			
		(Order separately).			
	19A700067P1 4029082P2	Receptacle, coax; sim to Amphenol 83-798.  Adaptor.			
	4029062F2				
Q202	19A134164P2 19A134239P3	Silicon, NPN; sim to Type 2N5945. Silicon, NPN.			
Q203LL Q203L	19A134239P3 19A134239P1	Silicon, NPN.			
Q203M	19A134239P1	Silicon, NPN.			
Q203H	19A134239P1	Silicon, NPN.			
Q204LL	19A134242P3	Silicon, NPN.			
Q204L	19A134242P3	Silicon, NPN.			
Q204H	19A134242P4	Silicon, NPN; 50 Watt.			
Q215	19A116753P1	Silicon, NPN.			
RT201	19A129379G1	Thermistor: 40K ohms ±20%, color code white; sim to Carborundum Type M0806J-5.			
W218	19A130552G1	Jumper.			
W220	19B227087G1	Jumper: 6 inches long.			
W221	19B227088G1	Jumper.			
W243	19A129312G6	Antenna cable: approx 10 inches long. (Includes J243 & P203).			
₩244	5491689P104	Cable, RF: approx 4 inches long, 350 VRMS, 500 VDC operating voltage.			
		40 WATT MODULE 19C32134705 406-420 MHz (LL) 19C32134706 450-470 MHz (L) 19C32134707 470-494 MHz (M) 19C32134708 494-512 MHz (H) 19C32134709 420-450 MHz (LL)			

19A116655P20

19A116192P1

PARTS LIST	SYMBOL	GE PART NO.	DESCRIPTION
	C204	19A116655P20	Ceramic disc: 1000 pF +10%, 1000 VDCW; sim to
LBI30594G MHz. 40 WATT POWER AMPLIFIER	C205	19A116656P3J0	RMC Type JF Discap.  Ceramic disc: 3 pF $\pm$ 0.5 pF, 500 VDCW, temp coef
, G36 (CONTINUOUS DUTY) 25, G37 (CONTINUOUS DUTY - DUPLEX)	C206*	19A134666P1	O PPM.  Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G5 by REV L. Deleted in G6 by REV K. Delted in G7, G8 by REV
DESCRIPTION			H. Deleted in G9 by REV D. In 19C321347G5 off REV E & earlier: In 19C321347G6,G7,G8 REV C & earlier:
		19A116655PlS	Ceramic disc: 680 pF $\pm$ 10%, 1000 VDCW; sim to RMC
CAPACITORS	C207LL	19A116656P8J0	Type JF Discap.  Ceramic disc: 8 pF $\pm$ 0.5 pF, 500 VDCW; temp coef
Ceramic: 0.01 uF -0 +100%, 500 VDCW, rated 20	(207LL	1941100301000	O PPM.
amps; sim to Erie 327050X5W0103P.	C207L*	19A116656P9J0	Ceramic disc: 9 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.
Ceramic disc: 2.2 pF ±0.1 pF, temp coef 0 ±120 PPM. Added to G6 by REV C, G23 by REV D.			In REV D & earlier:
		19A116656P6J0	Ceramic disc: 6 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.
TERMINALS	C207M*	19A116656P7J0	Ceramic disc: 7 pF ±0.5 pF, 500 VDCW, temp coef
Solderless terminal.			0 РРМ.
Solderless terminal.		19A116656P6J0	In REV E & earlier:  Ceramic disc: 6 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.
JACKS AND RECEPTACLES	C207H	19A116656P6J0	Ceramic disc: 6 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.
Connector/cable: approx. 10 inches long.	C208LL	19A116656P8J0	Ceramic disc: 8 pF ±0.5 pF, 500 VDCW; temp coef
PLUGS	C208L*	19A116656P6J0	O PPM.  Ceramic disc: 6 pF ±0.5 pF, 500 VDCW, temp coef
Connector. Includes receptacle and adaptor. (Order separately).			O PPM. Deleted by REV E.
Receptacle, coax; sim to Amphenol 83-798.	C208M*	19A116656P6J0	Ceramic disc: 6 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM. Deleted by REV F.
Adaptor.	С208Н*	19A116656P6J0	Ceramic disc: 6 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM. Deleted by REV F.
	C209*	19A116656P33J0	Ceramic disc: 33 pF +5%, 500 VDCW, temp coef 0
Silicon, NPN; sim to Type 2N5945.			PPM. Added to G5 by REV G, G6 by REV E, G7 & G8 by REV F.
Silicon, NPN. Silicon, NPN.	C209LL*	7489162P15	Silver mica: 33 pF ±5%, 500 VDCW; sim. to Spragu Type 118. Deleted by REV C. Added by REV D. Deleted by REV G.
Silicon, NPN.	C209L*	7489162P11	Silver mica: 22 pF ±5%, 500 VDCW; sim to Spragu Type 118. Deleted by REV C.
Silicon, NPN.	C209M*	7489162P11	Silver mica: 22 pF ±5%, 500 VDCW; sim to Spragu
Silicon, NPN. Silicon, NPN.			Type 118. Deleted by REV C.  Silver mica: 27 pF ±5%, 500 VDCW; sim. to Spragu
Silicon, NPN; 50 Watt.	C209H*	7489162P13	Type 118. Deleted by REV C.
Silicon, NPN.	C210LL*	19A134666P3	Frequency network: selective, 400-500 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Deleted in G5 by REV L.
THERMISTORS	C210L*	19A134666P1	Deleted in G9 by REV D.  Frequency network: selective, 470-630 MHz res.
Thermistor: 40K ohms ±20%, color code white; sim to Carborundum Type Mo806J-5.	521011*	15115455571	freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G6 by REV K.
	C210M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G7 by REV H.
Jumper: Jumper: 6 inches long.	C210H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron
Jumper.		40.45.55	TC501:NPO:240J:SLAC. Deleted in G8 by REV H.
Antenna cable: approx 10 inches long. (Includes J243 & P203).	C211LL*	19A134666P3	Frequency network: selective, 400-500 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Deleted in G5 by REV L. Deleted in G9 by REV D.
Cable, RF: approx 4 inches long, 350 VRMS, 500 VDC operating voltage.	C211L*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron
40 WATT MODULE 19C32134705 406-420 MHz (LL) 19C32134706 450-470 MHz (L) 19C32134707 470-494 MHz (M)	C211M*	19A134666P1	TC501:NPO:240J:SLAC. Deleted in G6 by REV K.  Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron
19C321347GF 470-494 MHz (W) 19C321347GB 494-512 MHz (B) 19C321347G9 420-450 MHz (LL)	C211H*	19A134666P1	TC501:NPO:240J:SLAC. Deleted in G7 by REV H.  Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron
			TC501:NPO:240J:SLAC. Deleted in G8 by REV H.
Ceramic disc: 1000 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap.	C212	19A116192P1	Ceramic: 0.01 uF ±20%, 50 VDCW; sim to Erie 812 SPECIAL.
Ceramic: 0.01 uF ±20%, 50 VDCW; sim to Erie 8121 SPECIAL.			
	I	I	

SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART N
C213*	19A116656P4J0	Ceramic disc: 4 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM. Deleted by REV B.	C226L C226M	19A700131P4
C213LL*	19A116656P5J0	Ceramic dis: 5 pF +0.5 pF, 500 VDCW, temp coef 0 PPM. Added by REV E. Deleted by REV M. Added	C226H	19A700131P3
C214LL*	19A134666P3	by REV N.  Frequency network: selective, 400-500 MHz res. freq, 500 VDCW; sim to Dilectron	C227LL C227L	19A700131P4
00141+	10410400001	TC501:NPO:330J;SLAC. Deleted in G5 by REV L. Deleted in G9 by REV D.	C227M C227H	19A700131P3
C214L*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G6 by REV K.	C228	19A116655P2
C214M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G7 by REV H.	C229LL*	19A134666P3
C214H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G8 by REV H.	C229L*	19A134666P1
C215LL	19A700131P47	Metallized teflon: 47 pF ±2%, 250 VDCW.		
C215L	19A700131P47	Metallized teflon: 47 pF ±2%, 250 VDCW.	C229M*	19A134666P1
C215M	19A700131P43	Metallized teflon: 43 pF ±2%, 250 VDCW.		
C215H	19A700131P43	Metallized teflon: 43 pF ±2%, 250 VDCW.	C229H*	19A134666P
C216LL	19A700131P51	Metallized teflon: 51 pF ±2%, 250 VDCW, temp coef -130 PPM	C230LL*	19A116656P7
C216L	19A700131P43	Metallized teflon: 43 pF ±2%, 250 VDCW.		
C216M	19A700131P43	Metallized teflon: 43 pF ±2%, 250 VDCW.		
C216H	19A700131P39	Metallized teflon: 39 pF ±2%, 250 VDCW.	!	19A116656P
C217LL	19A116679P18D	Metallized teflon: 18 pF ±0.5 pF, 250 VDCW.		
C217L	19A116679P16D	Metallized teflon: 16 pF ±0.5 pF, 250 VDCW.	C230L*	19A116656P
C217M	19A116679P15D	Metallized teflon: 15 pF ±0.5 pF, 250 VDCW.	C230M	19A116656P
C217H	19A116679P13D	Metallized teflon: 13 pF ±0.5 pF, 250 VDCW.		
C218*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G5 by REV L. Deleted in G6 by REV K. Deleted in G7, G8 by REV	C230H	19A116656P
		H. Deleted in G9 by REV D.	1	
C219*	19A116655P18	Ceramic disc: 680 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap. Deleted in G6 by REV J. Addeed to G6 by REV M.	C232 C233L*	19B209723P
C219L*	19A116656P24J0	Ceramic disc: 24 pF ±5%, 500 VDCW, temp coef 0 PPM. Added to G6 by REV J. Deleted in G6 by REV M.	С233Н*	19A134100P
C220	19A116655P20	Ceramic disc: 1000 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap.	C234LL*	19A134666P
C221	19B209723P4	Tantalum: 6.8 uF <u>+</u> 20%, 35 VDCW.		
C222LL*	19A134666P3	Frequency network: selective, 400-500 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Deleted in G5 by REV L.	C234L*	19A134666P
C222L*	19A134666P1	Deleted in G9 by REV D.  Frequency network: selective, 470-630 MHz res.	C234M*	19A134666P
C222M*	19A134666P1	freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G6 by REV K. Frequency network: selective, 470-630 MHz res.	C234H*	19A134666P
G000#	19A134666P1	freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G7 by REV H.	C235LL*	19A700131P
C222H*	19813400071	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G8 by REV H.		
C223	19A116655P20	Ceramic disc: 1000 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap.	C235L	19A116952P
C224LL	19A700131P41	Metallized teflon: 41 pF ±2%, 250 VDCW, temp coef 0 -130 PPM.	C235M	19A700131F
C224L	19A700131P35	Teflon/mica: 35 pF ±2%, 250 VDCW.	C235H	19A700131P
C224M	19A700131P35	Teflon/mica: 35 pF ±2%, 250 VDCW.	C236LL*	19A700131P
C224H	19A700131P32	Metallized teflon: 32 pF ±2%, 250 VDCW.	1	l
C225LL	19A700131P43	Metallized teflon: 43 pF ±2%, 250 VDCW.		19A116952P
C225L	19A700131P35	Teflon/mica: 35 pF ±2%, 250 VDCW.	C236L	19A700131F
C225M	19A700131P33	Metallized teflon: 33 pF ±2%, 250 VDCW.	C236M	19A700131F
C225H	19A700131P32	Metallized teflon: 32 pF ±2%, 250 VDCW.	С236Н	19A700131F
C226LL	19A700131P47	Metallized teflon: 47 pF ±2%, 250 VDCW.		

DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION
letallized teflon: 43 pF ±2%, 250 VDCW.	C237LL	19A700131P47	Metallized teflon: 47 pF ±2%,
letallized teflon: 37 pF ±2%, 250 VDCW.	C237L*	19A700131P39	Metallized teflon: 39 pF ±2%,
Ceflon/mica: 35 pF ±2%, 250 VDCW.			In REV K & earlier:
letallized teflon: 43 pF ±2%, 250 VDCW.		19A116952P47	Metallized teflon: 47 pF ±2%, 2
tallized teflon: 37 pF ±2%, 250 VDCW.	C237M	19A700131P37	Metallized teflon: 37 pF ±2%,
allized teflon: 37 pF ±2%, 250 VDCW.	C237H*	19A700131P35	Teflon/mica: 35 pF <u>+</u> 2%, 250 VI
on/mica: 35 pF ±2%, 250 VDCW.			In REV D & earlier:
mic disc: 1000 pF ±10%, 1000 VDCW; sim to		19A116952P33	Metallized teflon: 33 pF ±2%,
Type JF Discap. quency network: selective, 400-500 MHz res.	C238LL	19A700131P47	Metallized teflon: 47 pF ±2%,
squency network. Selective, 400-300 min2 les. 194, 500 VDCW; sim to Dilectron 301:NPO:330J:SLAC. Deleted in G5 by REV L.	C238L	19A700131P43	Metallized teflon: 43 pF ±2%,
ted in G9 by REV D.	C238M*	19A700131P43	Metallized teflon: 43 pF ±2%,
uency network: selective, 470-630 MHz res.	1		In REV D & earlier:
NPO:240J:SLAC. Deleted in G6 by REV K.		19A116952P37	Metallized teflon: 37 pF ±2%,
uency network: selective, 470-630 MHz res. , 500 VDCW; sim to Dilectron	C238H*	19A700131P39	Metallized teflon: 39 pF ±2%,
PO:240J:SLAC. Deleted in G7 by REV H.			In REV D & earlier:
network: selective, 470-630 MHz res.		19A116952P33	Metallized teflon: 33 pF ±2%,
0:240J:SLAC. Deleted in G8 by REV H.  disc: 7 pF ±0.5 pF, 500 VDCW, temp coef	C239*	19A134666P1	Frequency network: selective, freq, 500 VDCW; sim to Dilectro TC501:NPO:240J:SLAC. Deleted
EV M & earlier: EV E & earlier:	C239LL*	7489162P13	Silver mica: 27 pF ±5%, 500 VD Type 118. Added to G5 by REV by REV L. Deleted in G9 by REV
isc: 8 pF ±0.5 pF, 500 VDCW; temp coef	C240LL*	19A134666P3	Frequency network: selective, freq, 500 VDCW; sim to Dilectr TC501:NPO:330J:SLAC. Deleted
sc: 4 pF +0.5 pF, 500 VDCW, temp coef leted by REV L.	C240L*	19A134666P1	Deleted in G9 by REV D.  Frequency network: selective, freq, 500 VDCW; sim to Dilectr
sc: 4 pF ±0.5 pF, 500 VDCW, temp coef	C240M*	19A134666P1	TC501:NPO:240J:SLAC. Deleted  Frequency network: selective, freq, 500 VDCW; sim to Dilectr
1000 pF <u>+</u> 10%, 1000 VDCW; sim to	C240H*	19A134666P1	TC501:NPO:240J:SLAC. Deleted Frequency network: selective,
6.8 uF ±20%, 35 VDCW.			freq, 500 VDCW; sim to Dilectr TC501:NPO:240J:SLAC. Deleted
: 2.2 pF ±0.1 pF, temp coef 0 ±120 d by REV B.	C241	19A134202P15	Tantalum: 6.8 uF ±20%, 35 VDC
sc: 2.2 pF ±0.1 pF, temp coef 0 ±120 ted by REV B.	C242	19A116655P20	Ceramic disc: 1000 pF ±10%, 1 RMC Type JF Discap.
etwork: selective, 400-500 MHz res.	C243	19A134202P15	Tantalum: 6.8 uF ±20%, 35 VDC
000 VDCW; sim to Dilectron NPO:330J:SLAC. Deleted in G5 by REV L. i in G9 by REV D.	C244 and C245	19A116655P18	Ceramic disc: 680 pF ±10%, 10 Type JF Discap.
network: selective, 470-630 MHz res. VDCW; sim to Dilectron 240J:SLAC. Deleted in G6 by REV K.	C246 thru C250	19A116655P20	Ceramic disc: 1000 pF ±10%, 1 RMC Type JF Discap.
network: selective, 470-630 MHz res. VDCW; sim to Dilectron	C251	19A116192P1	Ceramic: 0.01 uF ±20%, 50 VDC SPECIAL.
OJ:SLAC. Deleted in G7 by REV H. twork: selective, 470-630 MHz res.	C252LL*	19A116656P5J0	Ceramic dis: 5 pF ±0.5 pF, 50 pPM.
VDCW; sim to Dilectron 240J:SLAC. Deleted in G8 by REV H.		19A116656P9J0	In REV H-L:  Ceramic disc: 9 pF ±0.5 pF, 5
teflon: 47 pF ±2%, 250 VDCW.	1	1041100001900	O PPM.
REV M & earlier: REV E & earlier:			In REV B-G.
ed teflon: 43 pF <u>+</u> 2%, 250 VDCW.		19A116656P6J0	Ceramic disc: 6 pF ±0.5 pF, 5
ed teflon: 37 pF ±2%, 250 VDCW.			In REV A & earlier:
ica: 35 pF <u>+</u> 2%, 250 VDCW.	1	19A116656P4J0	Ceramic disc: 4 pF ±0.5 pF, 5
teflon: 33 pF <u>+</u> 2%, 250 VDCW.		1041100301490	0 PPM.
i teflon: 47 pF <u>+</u> 2%, 250 VDCW.	C252L*	19A116656P7J0	Ceramic disc: 7 pF ±0.5 pF, 5 0 PPM.
f REV M & earlier: f REV E & earlier:		1	In REV L:
ized teflon: 39 pF ±2%, 250 VDCW.		19A116656P3J0	Ceramic disc: 3 pF ±0.5 pF, 5 0 PPM.
on/mica: 35 pF ±2%, 250 VDCW.			In REV J-K:
zed teflon: 33 pF ±2%, 250 VDCW. zed teflon: 33 pF ±2%, 250 VDCW.		19A116656P7J0	Ceramic disc: 7 pF ±0.5 pF, 5 0 PPM.
		1	In REV B-H:

DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION
Metallized teflon: 47 pF ±2%, 250 VDCW.	C252M*	19A116656P4J0	Ceramic disc: 4 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM. Added by REV B.	L211	19B219457P6	Coil.
Metallized teflon: 39 pF ±2%, 250 VDCW.	C252H*	19A116656P3J0	Ceramic disc: 3 pF ±0.5 pF, 500 VDCW, temp coef	L212	19A701091G1	Coil.
In REV K & earlier:			O PPM. Added by REV B.			
Metallized teflon: 47 pF ±2%, 250 VDCW.	C253	19A116655P20	Ceramic disc: 1000 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap.	Q201	19A134237P1	Silicon, NPN.
Metallized teflon: 37 pF ±2%, 250 VDCW.  Teflon/mica: 35 pF ±2%, 250 VDCW.	C255 and	19A116655P18	Ceramic disc: 680 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap.			
In REV D & earlier:	C256			R201	19A700106P63	Composition: 1K ohms ±5%, 1/4 w.
Metallized teflon: 33 pF ±2%, 250 VDCW.	C257LL*	19A116656P5J0	Ceramic dis: 5 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.	R202	3R152P304J	Composition: 300K ohms ±5%, 1/4 w.
Metallized teflon: 47 pF ±2%, 250 VDCW.	1		In REV M:	R203*	19A700113P7	Composition: 4.7 ohms $\pm 5\%$ , $1/2$ w. Deleted by REV C. Added by REV D.
Metallized teflon: 43 pF ±2%, 250 VDCW.		19A116656P7J0	Ceramic disc: 7 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.	R204*	19A700113P25	Composition: 27 ohms ±5%, 1/2 w.
Metallized teflon: 43 pF ±2%, 250 VDCW.		:	In REV L & earlier:			In REV B & earlier:
In REV D & earlier:		19A116656P5J0	Ceramic dis: 5 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.		3R77P220J	Composition: 22 ohms ±5%, 1/2 w.
Metallized teflon: 37 pF ±2%, 250 VDCW.  Metallized teflon: 39 pF ±2%, 250 VDCW.	C257L*	19A134100P20	Ceramic disc: 2.2 pF +0.1 pF, temp coef 0 ±120	R205	19A700106P23	Composition: 22 ohms ±5%, 1/4 w.
In REV D & earlier:			PPM. Deleted by REV B.	R206 R207	19A700113P15 19A700106P35	Composition: 10 ohms $\pm 5\%$ , $1/2$ w. Composition: 68 ohms $\pm 5\%$ , $1/4$ w.
Metallized teflon: 33 pF ±2%, 250 VDCW.	C257M*	19A134100P19	Ceramic disc: 1 pF ±0.1 pF, temp coef 0 ±250 PPM. Deleted by REV B.	R208	19A700113P15	Composition: 10 ohms ±5%, 1/2 w.
Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron	C257H*	19A134100P19	Ceramic disc: 1 pF ±0.1 pF, temp coef 0 ±250 ppM. Deleted by REV B.	R209	19A700113P57	Composition: 560 ohms ±5%, 1/2 w.
TC501:NPO:240J:SLAC. Deleted from G5 by REV H.	C260	19A116655P20	Ceramic disc: 1000 pF ±10%, 1000 VDCW; sim to	R210 thru	19C850605P1	Shunt resistor.
Silver mica: 27 pF $\pm$ 5%, 500 VDCW; sim. to Sprague Type 118. Added to G5 by REV H. Deleted in G5 by REV L. Deleted in G9 by REV D.	C262*	19A116114P2044	RMC Type JF Discap. Ceramic: 27 pF +5%, 100 VDCW; temp coef -80 PPM. Added to G6 by REV F. Deleted by REV G.	R212 R213	19A116559P102	Variable cermet: 5000 ohms <u>+</u> 20%, 1/2 w; sim to CTS Series 360.
Frequency network: selective, 400-500 MHz res. freq, 500 VDCW; sim to Dilectron	C263*	19A116655P20	Ceramic disc: 1000 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap.	R214	19A700113P15	Composition: 10 ohms ±5%, 1/2 w.
TC501:NPO:330J:SLAC. Deleted in G5 by REV L. Deleted in G9 by REV D.	and C264*		Added to G5 by REV K. Added to G6 by REV H. Added to G7 & G* by REV G. Added to G9 by REV C.	R215	19A700106P25	Composition: 27 ohms ±5%, 1/4 w.
Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G6 by REV K.		·	DIODES AND RECTIFIERS	R216*	19A700113P15	Composition: 10 ohms ±5%, 1/2 w. Added to G6 by REV F. Deleted by REV L.
Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron	CR201	19A116052P1	Silicon, hot carrier: Fwd drop .350 volts max.			
TC501:NPO:240J/SLAC. Deleted in G7 by REV H.  Frequency network: selective, 470-630 MHz res.	CR202 thru CR205	19A115250P1	Silicon, fast recovery, 225 mA, 50 PIV.	T201 thru	19A130446G1	Coil.
freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G8 by REV H.	Chizot			T205		
Tantalum: 6.8 uF ±20%, 35 VDCW.  Ceramic disc: 1000 pF ±10%, 1000 VDCW; sim to	E201 and E202	19A134263P1	Contact, electrical: sim to Selectro 229-1082-00-0-590.	U201	19D423127G1	Power Control.
RMC Type JF Discap.  Tantalum: 6.8 uF ±20%, 35 VDCW.	G211	19A134263P1	Contact, electrical: sim to Selectro			
Ceramic disc: 680 pF ±10%, 1000 VDCW; sim to RMC			229-1082-00-0-590.	VR201	4036887P1	Zener: 500 mW, 2.3 v. nominal.
Type JF Discap.			JACKS AND RECEPTACLES	VR202	4036887P5	Zener: 500 mW, 5.4 v. nominal.
Ceramic disc: 1000 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap.	J201	19A700049P2	Connector, receptacle; 500 VDCW maximum; sim to NTTF-1058.			
Ceramic: 0.01 uF ±20%, 50 VDCW; sim to Erie 8121 SPECIAL.	J205	19B219374G1	Connector: 9 contacts.	W201 thru W205		(Part of printed board 19D423005P1).
Ceramic dis: 5 pF ±0.5 pF, 500 VDCW, temp coef 0				W206	19A701093P1	Strap.
PPM.	L202	19A701091G1 19A129774P1	Coil.	W209	19B226733G1	Jumper.
In REV H-L:	L203 L204	19A129774P1 19A701091G1	Coil.	W210	19B226734G1	Jumper.
Ceramic disc: 9 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.	L204	19B219457P6	Coil.			
In REV B-G.	L206	19A700000P120	Coil, RF: 5.6 uH ±10%; sim to Jeffers 4422-1K.	Z201*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron
Ceramic disc: 6 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.  In REV A & earlier:	L207*	19A700000P20	Coil, RF: 5.6 uH ±10%; sim to Jeffers 4421-4K. Deleted in G5 by REV M, G9 by REV E.			TC5Ói:NPO:240J:SLAC. Added to G5 by REV L. Added to G6 by REV K. Added to G7, G8 by REV H. Added to G9 by REV D.
Ceramic disc: 4 pF ±0.5 pF, 500 VDCW, temp coef	L208LL	19B219457P6	Coil.	Z203LL*	19A134666P3	Frequency network: selective, 400-500 MHz res. freq, 500 VDCW; sim to Dilectron
0 PPM.	L208L	19A130650P1	Coil.			TC501:NPO:330J:SLAC. Added to G5 by REV L. Added to G9 by REV D.
Ceramic disc: 7 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.	L208M L208H	19A130650P1 19A130650P1	Coil.	Z203L*	19A134666P1	Frequency network: selective, 470-630 MHz res.
In REV L:	L209	19A701091G1	Coil.			freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G6 by REV K.
Ceramic disc: 3 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.	L210LL*	19A700000P25	Coil, RF: 15 uH ±10%; sim to Jeffers 4421-9K. Deleted by REV M.	Z203M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G7 by REV H.
In REV J-K:	L210L	19A700000P20	Coil, RF: 5.6 uH ±10%; sim to Jeffers 4421-4K.	Z203H*	19A134666P1	Frequency network: selective, 470-630 MHz res.
Ceramic disc: 7 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.	L210M	19A700000P20	Coil, RF: 5.6 uH ±10%; sim to Jeffers 4421-4K.		l	freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G8 by REV H.
In REV B-H:	L210H	19A700000P20	Coil, RF: 5.6 uH ±10%; sim to Jeffers 4421-4K.			
Ceramic dis: 5 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.		1				
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SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION
Z204LL*	19A134666P3	Frequency network: selective, 400-500 MHz res. freq, 500 VDCW; sim to Dilectron TC501:MPO:330J:SLAC. Added to G5 by REV L.	Z211M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:2401;SLAC. Added to G7 by REV H.			LOW PASS FILTER MODULE 19C321424G4			ANTENNA MATCHER 19C330778G2
Z204L*	19A134666P1	Added to G9 by REV D.  Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron	Z211H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G8 by REV H.			(Deleted from 19D424895 by REV A)			CAPACITORS
Z204M*	19A134666P1	TC501:NPO:240J:SLAC. Added to G6 by REV K.  Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron	Z212*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G5 by REV L.	C4280H C4281H	19A116952P9 19A116952P18	Metallized teflon: 9 pF + or 0.5 pF, 250 VDCW.  Metallized teflon: 18 pF + 0.5 pF, 250 VDCW.	C1B	19A116192P2	Ceramic: 470 pF ±20%, 50 VDCW; sim to Erie 811-A050-W5R-471M.
Z204H*	19A134666P1	TC501:NPO:240J:SLAC. Added to G7 by REV H.  Frequency network: selective 470-630 MHz res			Added to G6 by REV K. Added to G7, G8 by REV H. Added to G9 by REV D.	C4282H	19A116952P12	Metallized teflon: 12 pF ±0.5 pF, 250 VDCW.	C2 C4B	19A700008P2 19A700008P1	Variable: 2.28 to 14.13 pF; sim to EF Johnson 187-0109-005.  Variable: 2.04 to 9.9 pF, 250V peak.
Z205LL*	19A134666P3	TC501:NPO:240J:SLAC. Added to G8 by REV H.  Frequency network: selective, 400-500 MHz res.	Z213* and Z214*		NETWORK ASSEMBLY 19A143581G1 (Added to G5 by REV M, G9 by REV E)	C4283H	19A700015P37	Teflon/Mica: 220 pF ±5%, 250 VDCW.			DIODES AND RECTIFIERS
		freq, 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Added to G5 by REV L. Added to G9 by REV D.				L4281 and L4282	19B226709G1	Jumper.	CR1	19A700047P3	Silicon: 100 mW; sim to 1N6263.
Z205L*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G6 by REV K.	L1 L2	19A700024P1	Coil, RF: 100 nH ±10%, 0.08 ohms DC res max, 100 v.			JACKS AND RECEPTACLES	L1B	19A143342P1	Coil.
Z205M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G7 by REV H.	LZ	19A701091G2	Co11.	J202 and J203	19A130924G1	Connector, receptacle: coaxial, jack type; sim to Cinch 14H11613.	R1	19A700106P31	
Z205H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G8 by REV H.	R1	19A700106P15	Composition: 10 ohms ±5%, 1/4 w.	J206 and J207		(Part of K201).		1011.001.001.01	-
Z206*	19A134666P1	Frequency network: selective, 470-630 MHz res.			LOW PASS FILTER 19C327024G1 406-450 MHz (LL) (Added to 19D424895G5 & G36 by REV A)	J208	4033513P4	Contact, electrical: sim to Bead Chain L93-3.			FRAME ASSEMBLY 19D417526G3
		TC501:NPO:240J:SLAC. Added to G5 by REV L. Added to G6 by REV K. Added to G7, G8 by REV H. Added to G9 by REV D.			19C327024G2 450-512 MHz (H) (Added to 19D424895G6-G8 by REV A)	K201	19A116722P1		W241	5491689P104	Cable, RF: approx 4 inches long, 350 VRMS, 500 VDC operating voltage.
Z207LL*	19A134666P3	Frequency network: selective, 400-500 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Added to G6 by REV L. Added to G9 by REV D.			19C327024G7 406-450 MHz (LL) DUPLEX (Added to 19D424895G22 & G37 by REV A) (Deleted in 19D424895G22 by REV C, G37 by REV B)			contact, 9.6 to 15.8 VDC (over the temp range indicated). (Includes J206 & J207).			MISCELLANEOUS
Z207L*	19A134666P1	Frequency network: selective, 470-630 MHz res.			19C327024G8 450-512 MHz (H) DUPLEX (Added to 19D424895G23-G25 by REV A)	W4280 thru				5492178P2	Washer, spring tension: sim to Wallace Barnes 375-20. (Used with Q202).
Z207M*	19A134666P1	TC501:NPO:240J:SLAC. Added to G6 by REV K.  Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron			(Deleted by REV C)	W4283				19A702182P1 19A702782P5	Spacer. (Used with Q202).  Nut, hex, brass: No. 8-32. (Used with Q202).
Z207H*	19A134666P1	TC501:NPO:240J:SLAC. Added to G7 by REV H.  Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron	C4290LL C4290H	19A700014P4 19A700131P9	Metallized teflon: 10 pF $\pm$ 5%, 250 VDCW.  Metallized teflon: 9 pF $\pm$ 0.5 pF, 250 VDCW.			LOW PASS FILTER-DUPLEX W MATCHER 19C327024G11 406-450 MHz (LL) (Added to 19D424895G22 by REV C, G37 by REV B)		N44P9010C6 N80P13016C6	Machine screw: No. 4-40 x 5/8. (Used with Q203).
Z208LL*	19A134666P3	TC501:NPO:240J:SLAC. Added to G8 by REV H. Frequency network: selective, 400-500 MHz res.	C4291LL	19A700131P20	Metallized teflon: 20 pF ±0.5 pF, 100 VDCW.			19C327024G12 450-512 MHz (H) (Added to 19D424895G23-G25 by REV C)		19B201074P306	Machine screw, phillips head: No. 6-32 x 1. (Secures Filter Assembly).  Tap screw, Phillips POZIDRIV®: No. 6-32 x 3/8.
		freq, 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Added to G5 by REV L. Added to G9 by REV D.	C4291H C4292LL	19A700131P18 19A700131P13	Metallized teflon: 18 pF ±0.5 pF, 250 VDCW.  Metallized teflon: 13 pF ±0.5 pF, 250 VDCW.			LOW PASS FILTER 19D432247G3 406-450 MHz (LL) STATION		19C321441P1	(Secures G4214).  Insulator. (Located under 40 watt Module).
Z208L*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G6 by REV K.	C4292H C4293	19A700131P12 19A700015P37	Teflon: 12 pF ±0.5 pF, 250 VDCW. Teflon/Mica: 220 pF ±5%, 250 VDCW.			19D432247G4 450-512 MHz (H) STATION		19A701332P4 N210P9C	Insulator, washer: nylon. (Used with Q201).  Hex nut: No. 4-40. (Secures Q215).
Z208M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G7 by REV H.				C4290LL	19A700014P4	Metallized teflon: 10 pF ±5%, 250 VDCW.		19A115222P3 N80P9007C6	Insulator, bushing: (Secures Q215).  Machine screw, phillips: No. 4-40 x 7/16.
Z208H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:24UJ:SLAC. Added to G8 by REV H.	L4291LL L4291H	19B226709G2 19B226709G1	Jumper. (Includes L4292LL). Jumper. (Includes L4292H).	C4290H C4291LL	19A700131P9 19A700131P20	Metallized teflon: 9 pF ±0.5 pF, 250 VDCW.  Metallized teflon: 20 pF ±0.5 pF, 100 VDCW.		19B201074P308	(Secures Q215).  Tap screw, Phillips POZIDRIV®: No. 6-32 x 1/2.
Z209LL*	19A134666P3	Frequency network: selective, 400-500 MHz res. freq. 500 VDCW: sim to Dilectron	L4292LL L4292H		(Part of L4291LL). (Part of L4291H).	C4291H C4292LL	19A700131P18 19A700131P13	Metallized teflon: 18 pF ±0.5 pF, 250 VDCW.  Metallized teflon: 13 pF ±0.5 pF, 250 VDCW.		7150186P115	(Secures Filter Board).  Spacer: No. 6 x 1/2. (Located at junction of W221).
Z209L*	19A134666P1	TC501:NPO:330J:SLAC. Added to G5 by REV L. Added to G9 by REV D.  Frequency network: selective, 470-630 MHz res.			JACKS AND RECEPTACLES	C4292H C4293	19A700131P12 19A700015P37	Teflon: 12 pF ±0.5 pF, 250 VDCW.  Teflon/Mica: 220 pF ±5%, 250 VDCW.		19B219404G1	Web filter.
Z209M*		freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G6 by REV K.	J202 and J203	19A700049P2	Connector, receptacle; 500 VDCW maximum; sim to NTTF-1058.		323.00340.	INDUCTORS		19B201074P312 19B226212G1	Tap screw, Phillips POZIDRIV®: No. 6-32 x 3/4. (Secures W221 to spacer).  Heat sink. (Center sections-Quantity 3).
	19A134666P1	Frequency network: selective, 470~630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G7 by REV H.	J206 and J207	19A134263P2	Contact, electrical: sim to Selectro 229-1071.	L4291LL L4291H	19B226709G2 19B226709G1	Jumper. (Includes L4292LL). Jumper. (Includes L4292H).		19B226212G3 19D417513G1	Heat sink. (Caution nameplate end-Quantity 1).
Z209H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G8 by REV H.	J208	4033513P4	Contact, electrical: sim to Bead Chain L93-3.	L4292LL L4292H		(Part of L4291LL).		7139898P3	Cover, Heat Sink Assembly.  Nut, hex, brass: No. 1/4-28. (Secures C297).
Z210*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G5 by REV L.	K201	19A700061P1		L423211		(Part of L4291H).		19B201074P204 19A134260P1	Tap screw, phillips POZIDRIV®: No. 4-40 x 1/4. (Secures W241).  Cover, Insulator. (Used with Q215).
Z211LL*	19A134666P3	Added to G6 by REV K. Added to G7, G8 by REV H. Added to G9 by REV D.  Frequency network: selective, 400-500 MHz res.			8-16.3 VDC; sim to GE 3SAV1760A2, CP Clare HFW-1201558, or Potter-Brumfield HCM6160.	J203	19A700049P2	Connector, receptacle; 500 VDCW maximum; sim to NTTF-1058.		4029974P1	Insulator, plate: aluminum. (Located under Q215).
		freq, 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Added to G5 by REV L. Added to G9 by REV D.	W4280			J4201 thru J4204	19A116364P2	Contact, electrical; sim to AMP 86182-7 (LOOSE PIECE).			
Z211L*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq, 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G6 by REV K.	thru W4283 W4284	19A130607G3	Cable, RF: approx .7 of an inch.						
		The color by his at				W4280 thru W4282		(Part of printed board 19D432087P2).			

PRODUCTION CHANGES

Changes in the equipment to improve performance or to simplify circuits are identified by a "Revision Letter," which is stamped after the model number of the unit. The revision stamped on the unit includes all previous revisions. Refer to the Parts List for descriptions of parts affected by these revisions.

REV. M - 40-Watt Module 19C321347G5 REV. E - 40-Watt Module 19C321347G9

REV. N - 40-Watt Module 19C321347G5

REV. F - 40-Watt Module 19C321347G9

REV. L - 40-Watt Module 19C321347G6

REV. M - 40-Watt Module 19C321347G6

To improve power output across the board. Deleted C213LL, L207 and L210LL. Added Z213 and Z214. Changed C257LL, C252LLB (Group 5 only), and Q203LLB.

To improve power output. Changed C230LL, C235LL, C236LL and C257LL. Added C213LL.

To increase power output. Changed C252LB and C237. Deleted R216 and C230.

To improve power output over the 450-470 MHz range. Changed C219L and C252L.

- REV. A PA Assembly 19D424895G5-G8, G22-G25
- To incorporate new low-pass filter. Deleted 19C321424. Added 19C327024.
- REV. A 40 Watt Module 19C321347G5-G8
- To improve power output at cold temperatures. Added CR204 & CR205.
- REV. B 40 Watt Module 19C321347G5-G8
- To improve operation.
  In 19032134765: deleted C213 and Changed C252LLB.
  In 19032134766: deleted C237L, C257L and added C252LB.
  In 19032134767: deleted C257M and added C252MB.
  In 19032134768: deleted C233H, C257H and added C252HB.
- REV. C 40 Watt Module 19C321347G5-G8
- To improve operation, Deleted C209 and R203, Changed R204,
- REV. D 40 Watt Module 19C321347G5
  - To improve operation. Added C209 and R203.
- REV. E 40 Watt Module 19C321347G5 To improve station operation. Added C213.
- REV. D 40 Watt Module 19C321347G6-G8
- To improve operation. Changed C206. REV. F - 40 Watt Module 19C321347G5
- To improve operation. Changed C206.
- REV. E 40 Watt Module 19C321347G7, G8
- To improve RF output & efficiency. Changed C237 (Group 8) and C238 (Groups 7 & 8).
- REV. G 40 Watt Module 19C321347G5
- REV. E 40 Watt Module 19C321347G6 REV. F - 40 Watt Module 19C321347G7, G8
- To decrease spurious outputs. Changed C207L, M and C209. Deleted C208L, M, H. Added R203 to Groups 6, 7 and 8.
- REV. H 40 Watt Module 19C321347G5
- To increase output at 406 MHz. Changed C252LLB. Deleted C239. Added C239LLB.
- REV. J To improve stability. Changed Q203LL.
- REV. F 40 Watt Module 19C321347G6
- To improve stability. Added R216 and C262.
- REV. G To improve operation. Deleted C262.
- REV. A 40 Watt Module 19C321347G9 To improve operation. Added C240LL.
- REV. B To improve stability. Changed Q203LL.
- REV. K 40 Watt Module 19C321347G5 REV. H - 40 Watt Module 19C321347G6
- REV. G 40 Watt Module 19C321347G7
- REV. G 40 Watt Module 19C321347G8
- REV. C 40 Watt Module 19C321347G9
- To improve operation of power regulator circuit when used as driver for 100 Watt PA. Added C263 and C264.
- REV. J 40 Watt Module 19C321347G6 To increase output power at low end of 450-470 MHz range. Changed C252.
- REV. L 40 Watt Module 19C321347G5
- REV. K 40 Watt Module 19C321347G6
- REV. H 40 Watt Module 19C321347G7
- REV. H 40 Watt Module 19C321347G8
- REV. D 40 Watt Module 19C321347G9 To incorporate new nomenclature for frequency selection networks.
- REV. A PA Assembly 19D424895G36, G37 REV. B PA Assembly 19D424895, G5-G8, G22-G25
- To improve operation of power control transistor. Changed Q215.
- REV. C PA Assembly 19D424895G6 REV. D PA Assembly 19D424895G23
- To improve power output. Added C299.
- REV. C PA Assembly 19D424895G22-G25 REV. B PA Assembly 19D424895G37

To improve operation in duplex applications. Changed low pass filters. (Added Antenna Matching Unit).

PARTS LIST

SYMBOL	GE PART NO.	DESCRIPTION
C1B	19A116192P2	Ceramic: 470 pf ±20%, 50 VDCW; sim to Erie 8111-A050-W5R-471M.
C2	19A700008P2	Variable, air: 2.28 to 14.13 pf, 250 v; sim to EF Johnson Type T 187-0109-005.
C4B	19A700008P1	Variable, air: 2.04 to 9.9 pf, 250 v; sim to EF Johnson Type T 187-0106-005.
CR1	19A700047P3	DIODES AND RECTIFIERS Diode, silicon: 0.410 volt max.
LlB	19A143342P1	
	·	RESISTORS
R1	19A700106P31	Composition: 47 ohms ±5%, 1/4 w.
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